

MOSFET - P-Channel, TSOP-6

-3.5 A, -30 V

NTGS3455T1

Features

- Ultra Low R_{DS(on)}
- Higher Efficiency Extending Battery Life
- Miniature TSOP-6 Surface Mount Package
- Pb-Free Package is Available

Applications

Power Management in Portable and Battery-Powered Products, i.e.:
 Cellular and Cordless Telephones, and PCMCIA Cards

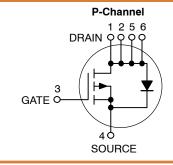
MAXIMUM RATINGS (T_J = 25 °C unless otherwise noted.)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	-30	Volts
Gate-to-Source Voltage - Continuous	V _{GS}	±20.0	Volts
Thermal Resistance Junction-to-Ambient (Note 1) Total Power Dissipation @ T _A = 25 °C Drain Current - Continuous @ T _A = 25 °C - Pulsed Drain Current (T _p < 10 μS) Maximum Operating Power Dissipation Maximum Operating Drain Current	R _B JA Pd I _D I _{DM} Pd I _D	62.5 2.0 -3.5 -20 1.0 -2.5	°C/W Watts Amps Amps Watts Amps
Thermal Resistance Junction-to-Ambient (Note 2) Total Power Dissipation @ T _A = 25 °C Drain Current - Continuous @ T _A = 25 °C - Pulsed Drain Current (T _p < 10 μS) Maximum Operating Power Dissipation Maximum Operating Drain Current	R _{eJA} Pd I _D I _{DM} Pd I _D	128 1.0 -2.5 -14 0.5 -1.75	°C/W Watts Amps Amps Watts Amps
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to 150	°C
Maximum Lead Temperature for Soldering Purposes for 10 Seconds	TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Mounted onto a 2" square FR-4 board (1 in sq, 2 oz. Cu. 0.06" thick single sided), t < 5.0 seconds.
- Mounted onto a 2" square FR-4 board (1 in sq, 2 oz. Cu. 0.06" thick single sided), operating to steady state.

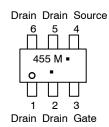
V _{(BR)DSS} R _{DS(on)} TYP		I _D Max
-30 V	100 mΩ @ –10 V	-3.5 A



MARKING DIAGRAM & PIN ASSIGNMENT



TSOP-6 CASE 318G STYLE 1



455 = Specific Device Code M = Date Code*

■ = Pb-Free Package

Application Note AND8002/D.

(Note: Microdot may be in either location) *For additional marking information, refer to

ORDERING INFORMATION

Device	Package	Shipping [†]
NTGS3455T1G	TSOP-6 (Pb-Free)	3000 / Tape & Reel

DISCONTINUED (Note 1)

NTGS3455T1	TSOP-6	3000 / Tape & Reel
		l

- †For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.
- DISCONTINUED: This device is not recommended for new design. Please contact your onsemi representative for information. The most current information on this device may be available on www.onsemi.com.

Downloaded from Arrow.com.

NTGS3455T1

ELECTRICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}\text{C}$ unless otherwise noted) (Notes 3 & 4)

Cha	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS		•		•	•	-
Drain-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = –10 μA)		V _{(BR)DSS}	-30	-	-	Vdc
Zero Gate Voltage Drain Current $(V_{GS} = 0 \text{ Vdc}, V_{DS} = -30 \text{ Vdc}, (V_{GS} = 0 \text{ Vdc}, V_{DS} = -30 \text{ Vdc},$	T _J = 25 °C) T _J = 70 °C)	I _{DSS}	- -	- -	-1.0 -5.0	μAdc
Gate-Body Leakage Current (V _{GS} = -20.0 Vdc, V _{DS} = 0 Vdc	:)	I _{GSS}	-	-	-100	nAdc
Gate-Body Leakage Current (V _{GS} = +20.0 Vdc, V _{DS} = 0 Vdc	:)	I _{GSS}	-	-	100	nAdc
ON CHARACTERISTICS						
Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = -250 \mu Adc$)		V _{GS(th)}	-1.0	-1.87	-3.0	Vdc
Static Drain-Source On-State Resistance ($V_{GS} = -10 \text{ Vdc}$, $I_D = -3.5 \text{ Adc}$) ($V_{GS} = -4.5 \text{ Vdc}$, $I_D = -2.7 \text{ Adc}$)		R _{DS(on)}	- -	0.094 0.144	0.100 0.170	Ω
Forward Transconductance (V _{DS} = -15 Vdc, I _D = -3.5 Adc)	9FS	-	6.0	-	mhos	
DYNAMIC CHARACTERISTICS						
Total Gate Charge		Q _{tot}	-	9.0	13	nC
Gate-Source Charge	$(V_{DS} = -15 \text{ Vdc}, V_{GS} = -10 \text{ Vdc}, I_{D} = -3.5 \text{ Adc})$	Q _{gs}	-	2.5	-	
Gate-Drain Charge	,	Q _{gd}	-	2.0	-	
Input Capacitance		C _{iss}	-	480	-	pF
Output Capacitance	$(V_{DS} = -5.0 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, f = 1.0 \text{ MHz})$	C _{oss}	-	220	-	
Reverse Transfer Capacitance	,	C _{rss}	-	60	_	
SWITCHING CHARACTERISTICS	5					
Turn-On Delay Time		t _{d(on)}	-	10	20	ns
Rise Time	$(V_{DD} = -20 \text{ Vdc}, I_D = -1.0 \text{ Adc},$	t _r	-	15	30	
Turn-Off Delay Time	$V_{GS} = -10 \text{ Vdc}, R_g = 6.0 \Omega$	t _{d(off)}	-	20	35	
Fall Time		t _f	-	10	20	
Reverse Recovery Time	$(I_S = -1.7 \text{ Adc}, dI_S/dt = 100 \text{ A/}\mu\text{s})$	t _{rr}	-	30	-	ns
BODY-DRAIN DIODE RATINGS						
Diode Forward On-Voltage	$(I_S = -1.7 \text{ Adc}, V_{GS} = 0 \text{ Vdc})$	V _{SD}	-	-0.90	-1.2	Vdc
Diode Forward On-Voltage	$(I_S = -3.5 \text{ Adc}, V_{GS} = 0 \text{ Vdc})$	V_{SD}	-	-1.0	-	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Indicates Pulse Test: P.W. = 300 μsec max, Duty Cycle = 2%.

4. Class 1 ESD rated – Handling precautions to protect against electrostatic discharge are mandatory.

NTGS3455T1

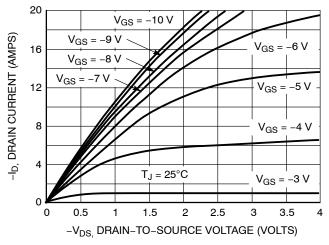


Figure 1. On-Region Characteristics

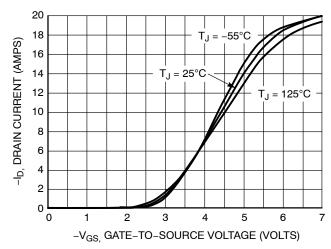


Figure 2. Transfer Characteristics

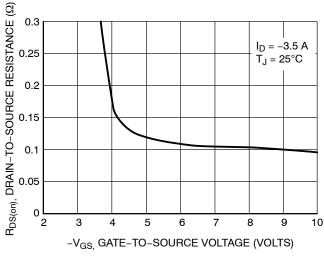


Figure 3. On-Resistance vs. Gate-to-Source Voltage

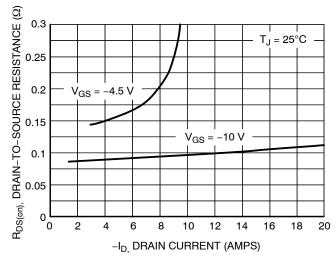


Figure 4. On-Resistance vs. Drain Current and **Gate Voltage**

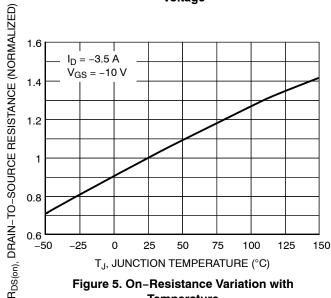


Figure 5. On-Resistance Variation with **Temperature**

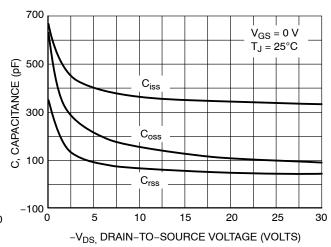
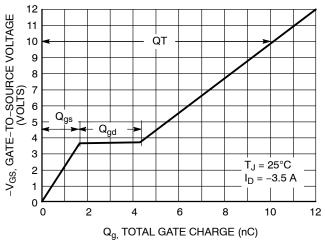


Figure 6. Capacitance Variation

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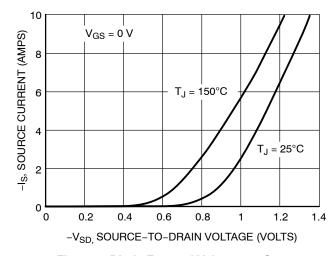


Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

Figure 8. Diode Forward Voltage vs. Current

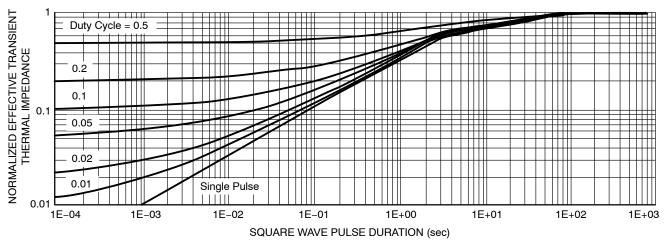


Figure 9. Normalized Thermal Transient Impedance, Junction-to-Ambient

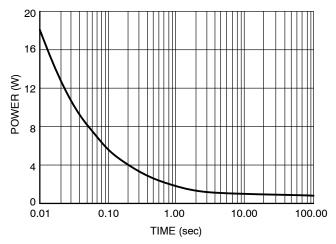


Figure 10. Single Pulse Power





NOTE 5

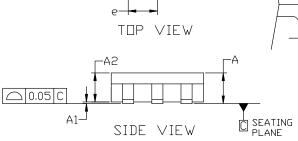
TSOP-6 3.00x1.50x0.90, 0.95P **CASE 318G ISSUE W**

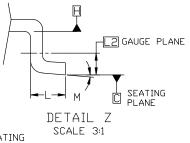
DATE 26 FEB 2024

NOTES

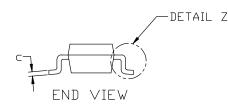
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM
 LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.

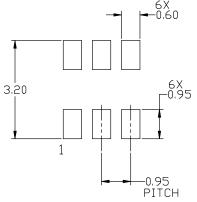
 5. PIN 1 INDICATOR MUST BE LOCATED IN THE INDICATED ZONE





\	MILLIM	IETER:	2
DIM	MIN	NDM	MAX
Α	0.90	1.00	1.10
A1	0.01	0.06	0.10
A2	0.80	0.90	1.00
b	0.25	0.38	0.50
\subset	0.10	0.18	0.26
D	2.90	3.00	3.10
Ε	2.50	2.75	3.00
E1	1.30	1.50	1.70
е	0.85	0.95	1,05
L	0.20	0.40	0.60
L2	0,25 BSC		
М	0°		10°





RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference manual, SDLDERRM/D.

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TSOP-6 3.00x1.50x0.90, 0.95P CASE 318G ISSUE W

DATE 26 FEB 2024

GENERIC MARKING DIAGRAM*



XXX M=
O =
1 U U
STANDARD

XXX = Specific Device Code

XXX = Specific Device Code

A =Assembly Location

M = Date Code

Y = Year

= Pb-Free Package

W = Work Week

r.

- 1 5 11001 401

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 2: PIN 1. EMITTER 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. BASE 2 6. COLLECTOR 2	STYLE 3: PIN 1. ENABLE 2. N/C 3. R BOOST 4. Vz 5. V in 6. V out	STYLE 4: PIN 1. N/C 2. V in 3. NOT USED 4. GROUND 5. ENABLE 6. LOAD	STYLE 5: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 6: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR
STYLE 7: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. N/C 5. COLLECTOR 6. EMITTER	STYLE 8: PIN 1. Vbus 2. D(in) 3. D(in)+ 4. D(out)+ 5. D(out) 6. GND	STYLE 9: PIN 1. LOW VOLTAGE GATE 2. DRAIN 3. SOURCE 4. DRAIN 5. DRAIN 6. HIGH VOLTAGE GATE	2. GND ' 3. D(OUT)- 4. D(IN)- 5. VBUS	STYLE 11: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1/GATE 2	STYLE 12: PIN 1. I/O 2. GROUND 3. I/O 4. I/O 5. VCC 6. I/O
STYLE 13: PIN 1. GATE 1 2. SOURCE 2 3. GATE 2 4. DRAIN 2 5. SOURCE 1 6. DRAIN 1	STYLE 14: PIN 1. ANODE 2. SOURCE 3. GATE 4. CATHODE/DRAIN 5. CATHODE/DRAIN 6. CATHODE/DRAIN		/LE 16: N 1. ANODE/CATHODE 2. BASE 3. EMITTER 4. COLLECTOR 5. ANODE 6. CATHODE	STYLE 17: PIN 1. EMITTER 2. BASE 3. ANODE/CATHODE 4. ANODE 5. CATHODE 6. COLLECTOR	

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